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Fig. 2

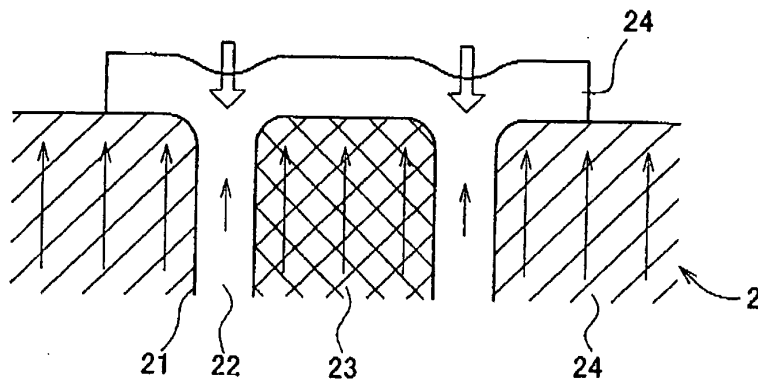


Fig. 3A

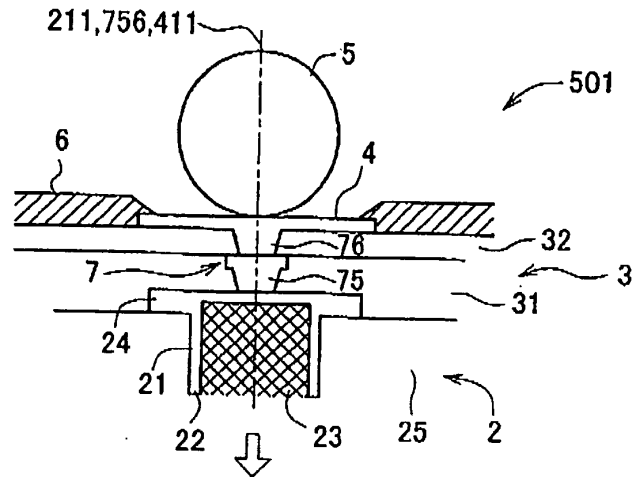


Fig. 3B

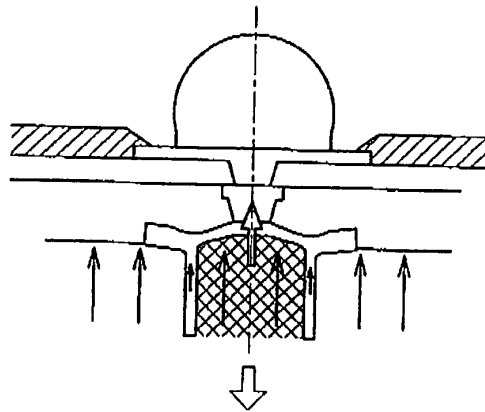


Fig. 3c

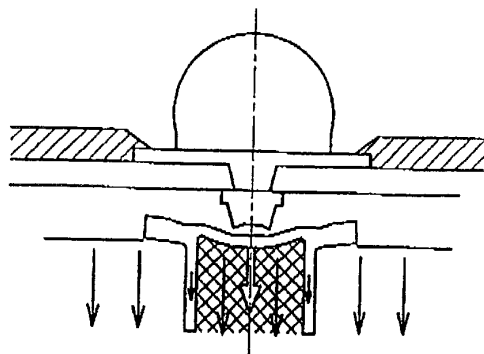


Fig. 4

	EXAMPLE	COMPARISON
①熱サイクル無し	0/30	8/17
②100サイクル後	0/30	26/51
③500サイクル後	0/30	10/18

- ① NO HEAT CYCLE
- ② AFTER 100 CYCLES
- ③ AFTER 500 CYCLES



Fig. 6

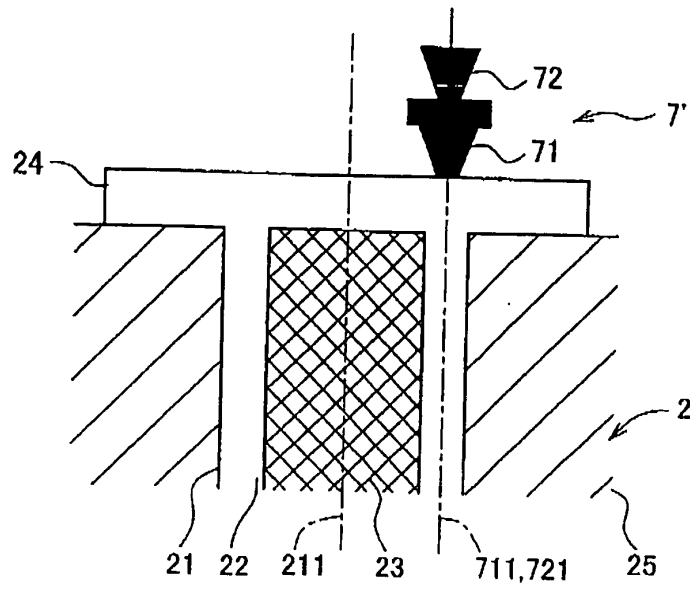


Fig. 7

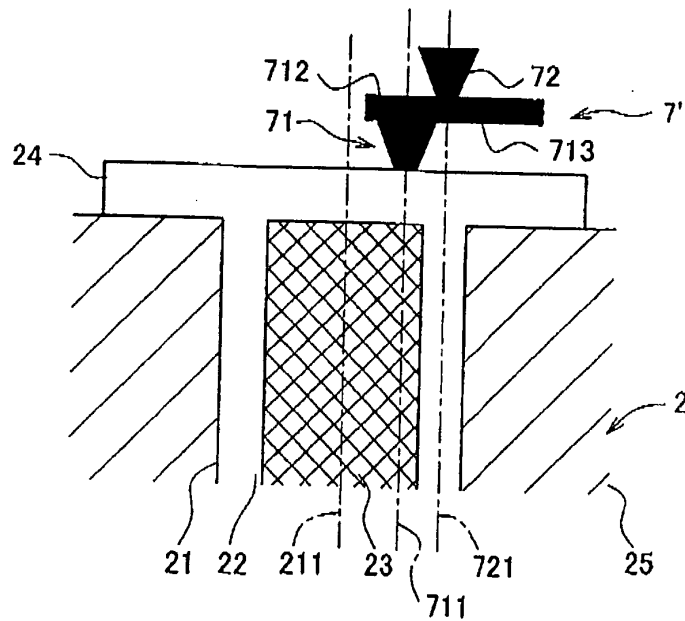


Fig. 8

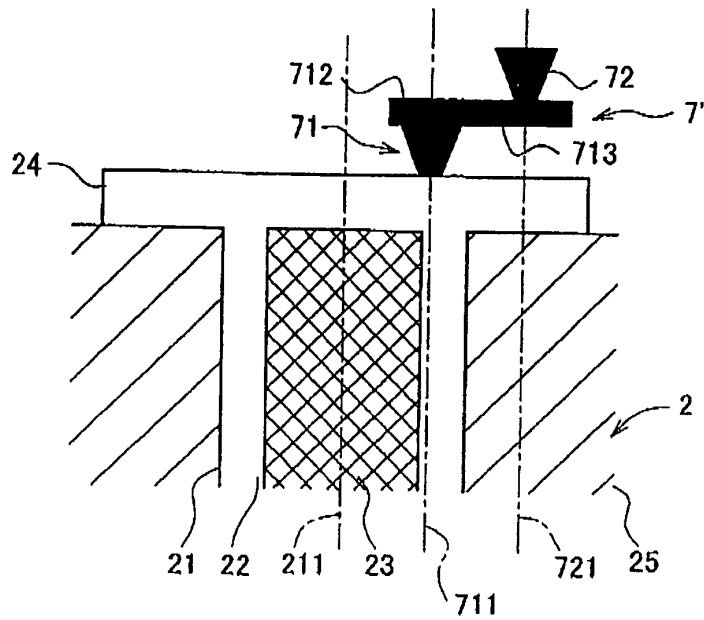
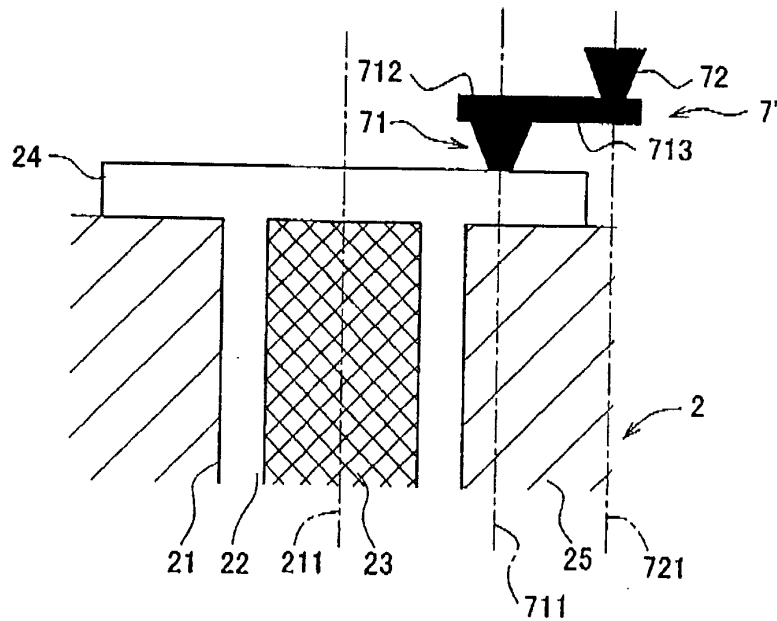


Fig. 9





A cross-sectional diagram of a semiconductor device assembly. The assembly includes a substrate 201 with a top layer 6. A central component 7 is positioned between two horizontal layers 31 and 32. Layer 31 has a patterned surface 241. To the right of component 7 is a hatched region 25. Below component 7 is a cross-hatched region 23. A vertical dimension PL is indicated from the bottom of component 7 to the top of the cross-hatched region 23. Other labels include 4, 42, 43, 5, 71, 72, 73, 81, and 91.